

Silicon NPN Power Transistors

2SC2582

DESCRIPTION

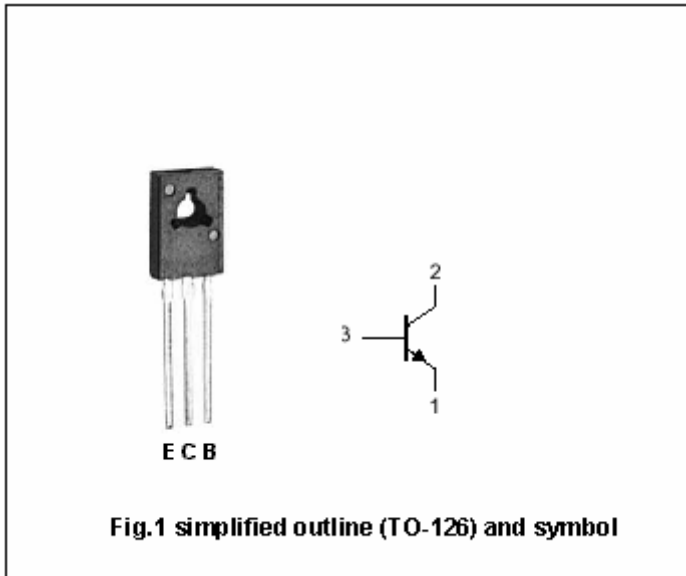
- With TO-126 package
- Large collector power dissipation
- High transition frequency

APPLICATIONS

- Audio frequency power amplifier

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CB0}	Collector-base voltage		45	V
V _{CEO}	Collector- emitter voltage		35	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		1	A
I _{CM}	Collector current-peak		1.5	A
P _C	Collector power dissipation	T _a =25°C	1.2	W
		T _C =25°C	10	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55°C+150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =2mA ; I _B =0	35			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	45			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =500mA ; I _B =50mA			0.5	V
I _{CEO}	Collector cut-off current	V _{CE} =20V ; I _B =0			100	μA
I _{CBO}	Collector cut-off current	V _{CB} =20V ; I _E =0			0.1	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V ; I _C =0			10	μA
h _{FE-1}	DC current gain	I _C =500mA ; V _{CE} =10V	85		340	
h _{FE-2}	DC current gain	I _C =1A ; V _{CE} =5V	50			
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =10V ; f=1MHz			20	pF
f _T	Transition frequency	I _C =50mA ; V _{CE} =10V		200		MHz

◆ h_{FE-1} Classifications

Q	R	S
85-170	120-240	170-340

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PACKAGE OUTLINE

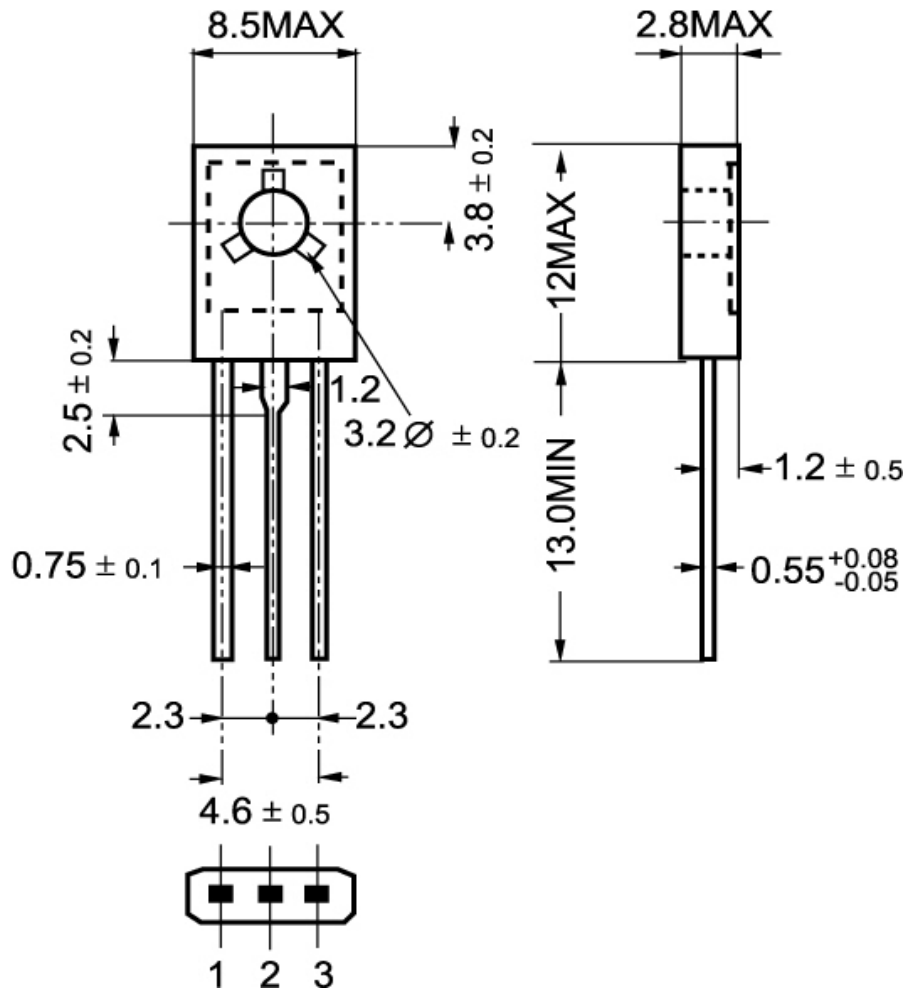


Fig.2 Outline dimensions